

## PNP SILICON POWER TRANSISTORS

...designed for use in low frequency power amplifier applications

### FEATURES:

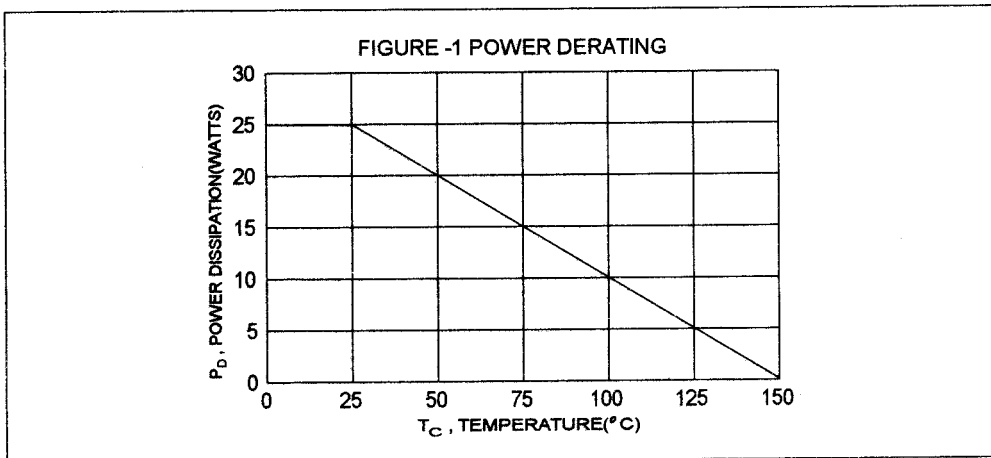
- \* Low Collector-Emitter Saturation Voltage  
 $V_{CE(sat)} = 1.0V(\text{Max}) @ I_C=2.0A, I_B=0.2A$
- \* DC Current Gain  
 $hFE = 35-320 @ I_C = 0.5A$
- \* Complementary to NPN 2SC1061

### MAXIMUM RATINGS

Characteristic	Symbol	2SA671	Unit
Collector-Emitter Voltage	$V_{CEO}$	50	V
Collector-Base Voltage	$V_{CBO}$	50	V
Emitter-Base Voltage	$V_{EBO}$	4.0	V
Collector Current - Continuous - Peak	$I_C$ $I_{CM}$	3.0 6.0	A
Base current	$I_B$	0.5	A
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	25 0.2	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

### THERMAL CHARACTERISTICS

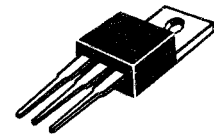
Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	$R_{\theta jc}$	5.0	$^\circ\text{C/W}$



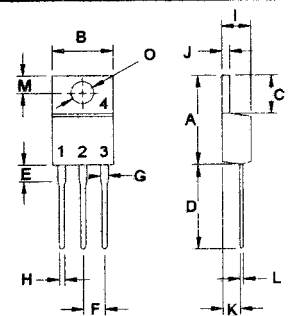
PNP  
2SA671

3.0 AMPERE  
SILICON POWER  
TRANSISTORS

50 VOLTS  
25 WATTS



TO-220



PIN 1. BASE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR(CASE)

DIM	MILLIMETERS	
	MIN	MAX
A	14.68	15.31
B	9.78	10.42
C	5.01	6.52
D	13.06	14.62
E	3.57	4.07
F	2.42	3.66
G	1.12	1.36
H	0.72	0.96
I	4.22	4.98
J	1.14	1.38
K	2.20	2.97
L	0.33	0.55
M	2.48	2.98
O	3.70	3.90

**ELECTRICAL CHARACTERISTICS** (  $T_c = 25^\circ\text{C}$  unless otherwise noted )

Characteristic	Symbol	Min	Max	Unit
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**OFF CHARACTERISTICS**

Collector-Emitter Voltage ( $I_C = 50 \text{ mA}$ , $I_B = 0$ )	$V_{CE0}$	50		V
Emitter-Base Voltage ( $I_B = 5.0 \text{ mA}$ , $I_C = 0$ )	$V_{EBO}$	7.0		V
Collector Cutoff Current ( $V_{CB} = 25 \text{ V}$ , $I_E = 0$ )	$I_{CBO}$		100	$\mu\text{A}$
Emitter Cutoff Current ( $V_{EB} = 4.0 \text{ V}$ , $I_C = 0$ )	$I_{EBO}$		100	$\mu\text{A}$

**ON CHARACTERISTICS (1)**

DC Current Gain ( $I_C = 0.1 \text{ A}$ , $V_{CE} = 4.0 \text{ V}$ ) * ( $I_C = 1.0 \text{ A}$ , $V_{CE} = 4.0 \text{ V}$ )	$h_{FE(2)}$ $h_{FE}$	35 35	320	
Collector-Emitter Saturation Voltage ( $I_C = 2.0 \text{ A}$ , $I_B = 200 \text{ mA}$ )	$V_{CE(sat)}$		1.0	V
Base-Emitter On Voltage ( $I_C = 1.0 \text{ A}$ , $V_{CE} = 4.0 \text{ V}$ )	$V_{BE(on)}$		1.5	V

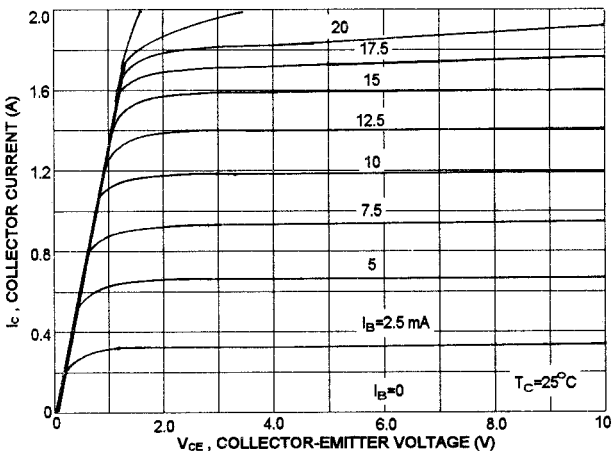
**DYNAMIC CHARACTERISTICS**

Current-Gain-Bandwidth Product ( $I_C = 0.5 \text{ A}$ , $V_{CE} = 4.0 \text{ V}$ , $f = 1.0 \text{ MHz}$ )	$f_T$	5.0		MHz
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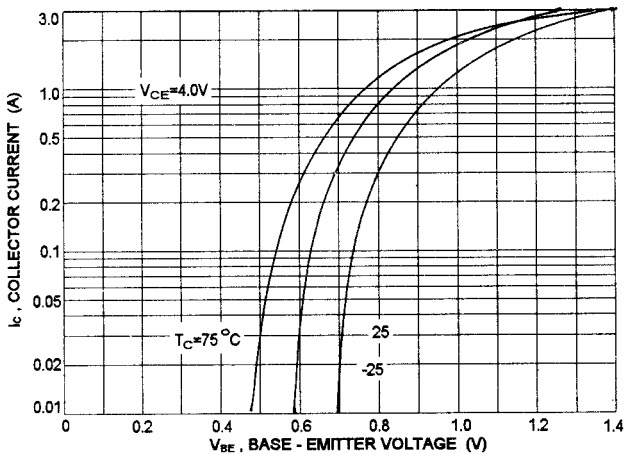
(1) Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ \*  $h_{FE(2)}$  Classification :

35	A	70	60	B	120	100	C	200	160	D	320
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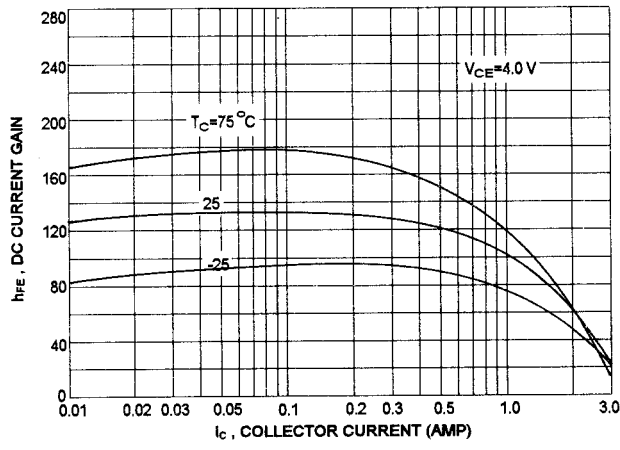
$I_c - V_{ce}$



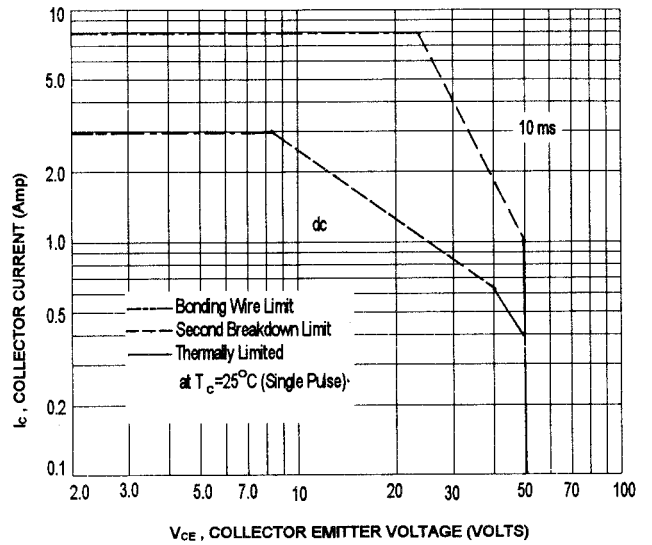
$I_c - V_{be}$



DC CURRENT GAIN



ACTIVE-REGION SAFE OPERATING AREA (SOA)



There are two limitation on the power handling ability of a transistor: average junction temperature and second breakdown safe operating area curves indicate  $I_c - V_{ce}$  limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than curves indicate.

The data of SOA curve is base on  $T_{J(PK)} = 150^\circ\text{C}$ ;  $T_c$  is variable depending on conditions. second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(PK)} < 150^\circ\text{C}$ . At high case temperatures, thermal limitation will reduce the power that can be handled to values less than the limitations imposed by second breakdown.